Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +85°C	I_D	8 6.4	A
Continuous Drain Current (Note 6) V_{GS} = 10V	t ≤ 10 sec	T_A = +25°C T_A = +85°C	I_D	10.7 8.6	A
Continuous Drain Current (Note 6) V_{GS} = 4.5V	t ≤ 10 sec	T_A = +25°C T_A = +85°C	I_D	9.6 7.7	A
Pulsed Drain Current (Note 7)			I_{DM}	45	A
Avalanche Current (Notes 7 & 8)			I_{AR}	13	A
Repetitive Avalanche Energy (Notes 7 & 8) L = 0.3mH			E_{AR}	25.4	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	1.54	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	81	°C/W
Power Dissipation (Note 6)	P_D	2.8	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 6)	$R_{\theta JA}$	45	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	150	μA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.3	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	11	15	mΩ	V_{GS} = 10V, I_D = 10.7A
		—	16.5	18.5		V_{GS} = 4.5V, I_D = 9.6A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	20	—	S	V_{DS} = 5V, I_D = 10.7A
Diode Forward Voltage	V_{SD}	—	0.36	0.5	V	V_{GS} = 0V, I_S = 1A
Maximum Body-Diode + Schottky Continuous Current	I_S	—	—	5	A	—
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	1849	—	pF	V_{DS} =15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	158	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	123	—	pF	
Gate Resistance	R_g	0.54	2.0	4.0	Ω	V_{DS} =0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge V_{GS} = 4.5V	Q_g	—	18.5	—	nC	V_{DS} = 15V, V_{GS} = 10V, I_D = 9.6A
Total Gate Charge V_{GS} = 10V	Q_g	—	43	—	nC	
Gate-Source Charge	Q_{gs}	—	4.7	—	nC	
Gate-Drain Charge	Q_{gd}	—	4.0	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	6.62	—	ns	V_{GS} = 10V, V_{DS} = 15V, R_G = 3Ω, R_L = 15Ω, I_D = 1A
Turn-On Rise Time	t_r	—	8.73	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	36.41	—	ns	
Turn-Off Fall Time	t_f	—	4.69	—	ns	

Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout. The value in any given application depends on the user's specific board design.
6. Device mounted on 1" × 1" FR-4 PCB with high coverage 1 oz. Copper, single sided, device is measured at t ≤ 10 sec.
7. Repetitive rating, pulse width limited by junction temperature.
8. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to production testing.

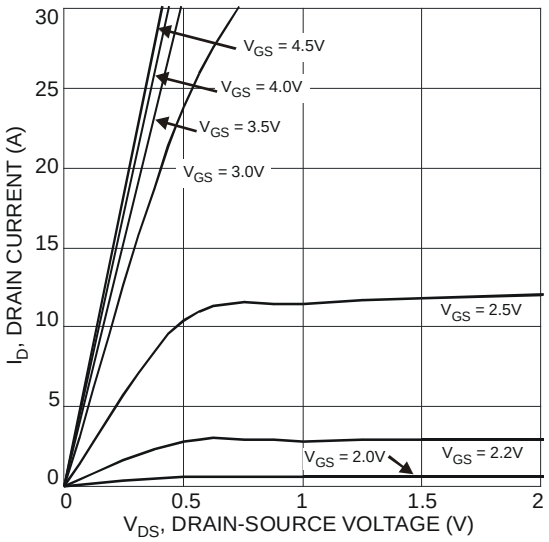


Fig. 1 Typical Output Characteristic

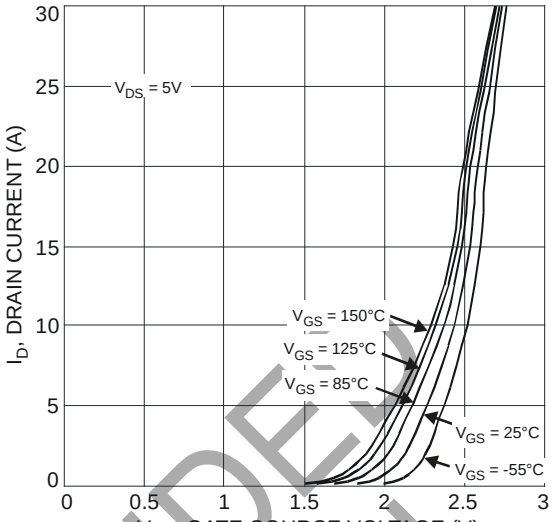


Fig. 2 Typical Transfer Characteristic

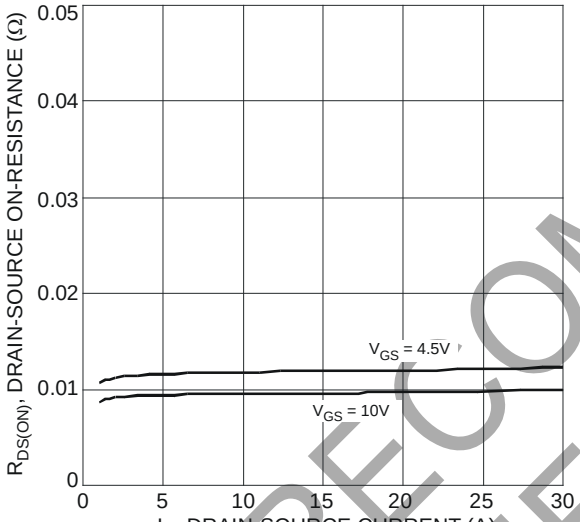


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

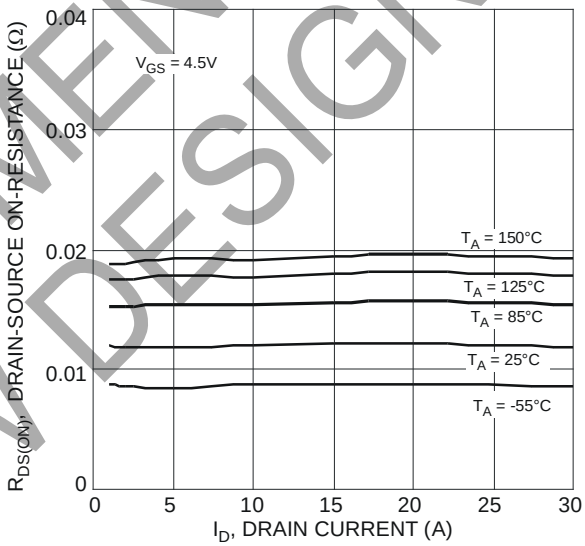


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

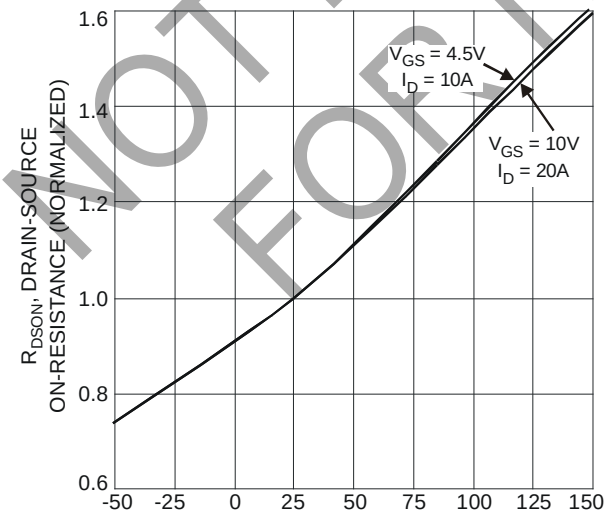


Fig. 5 On-Resistance Variation with Temperature

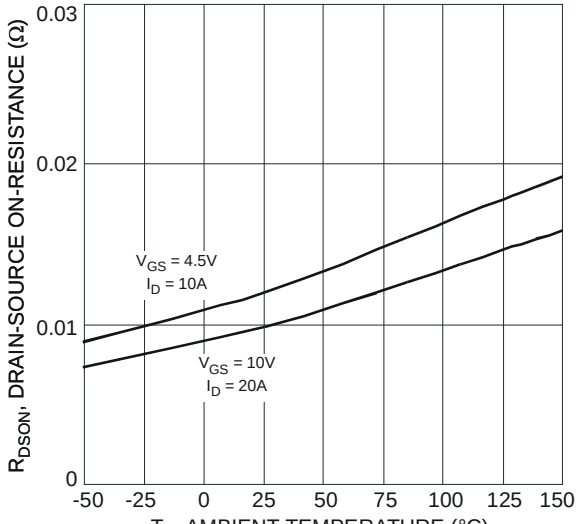


Fig. 6 On-Resistance Variation with Temperature

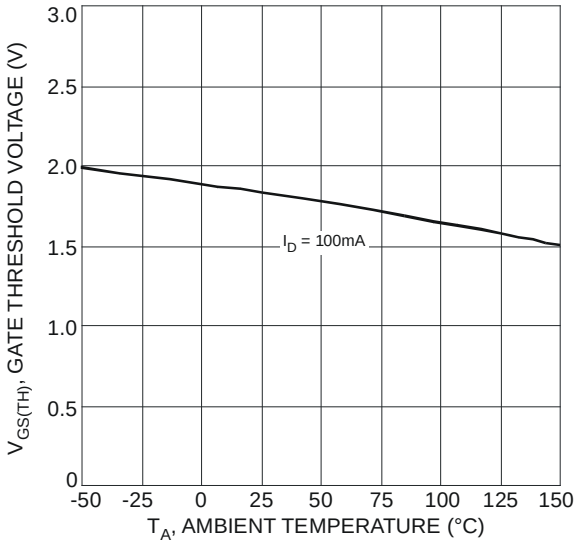


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

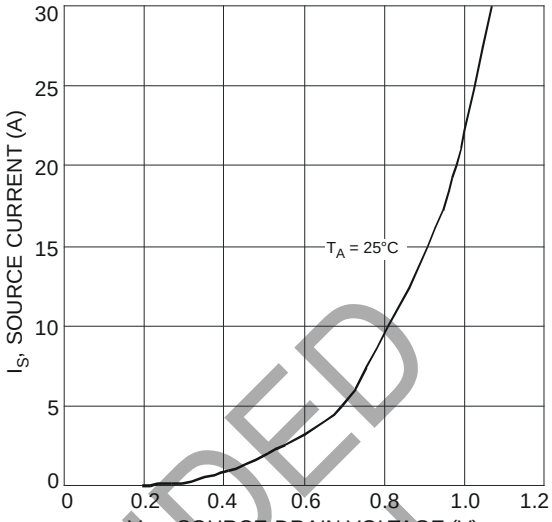


Fig. 8 Diode Forward Voltage vs. Current

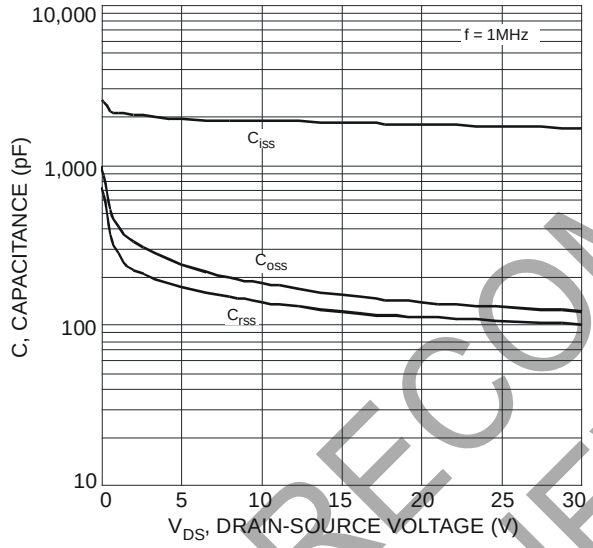


Fig. 9 Typical Total Capacitance

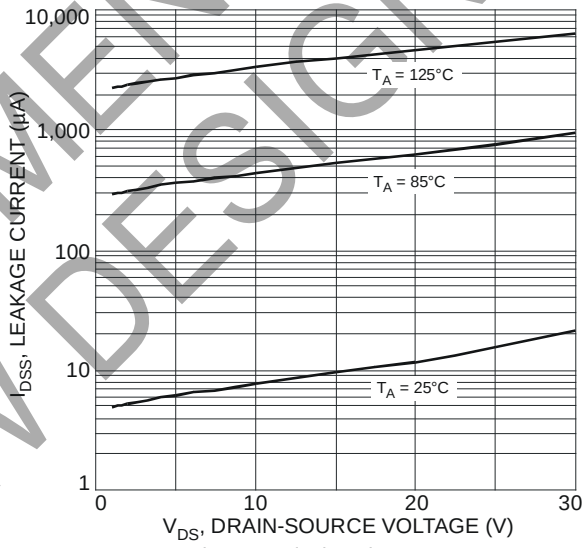


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

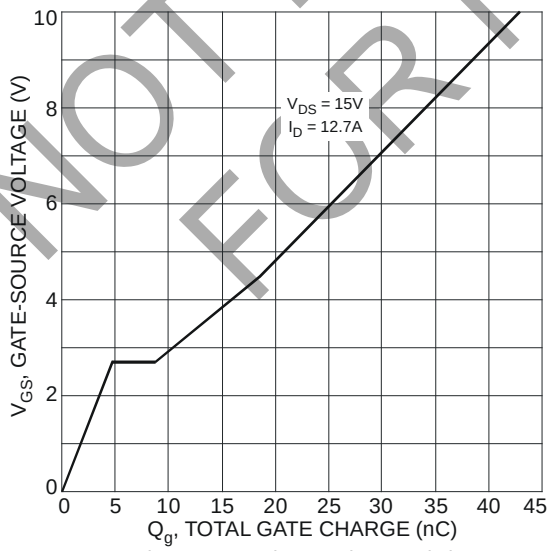


Fig. 11 Gate-Charge Characteristics

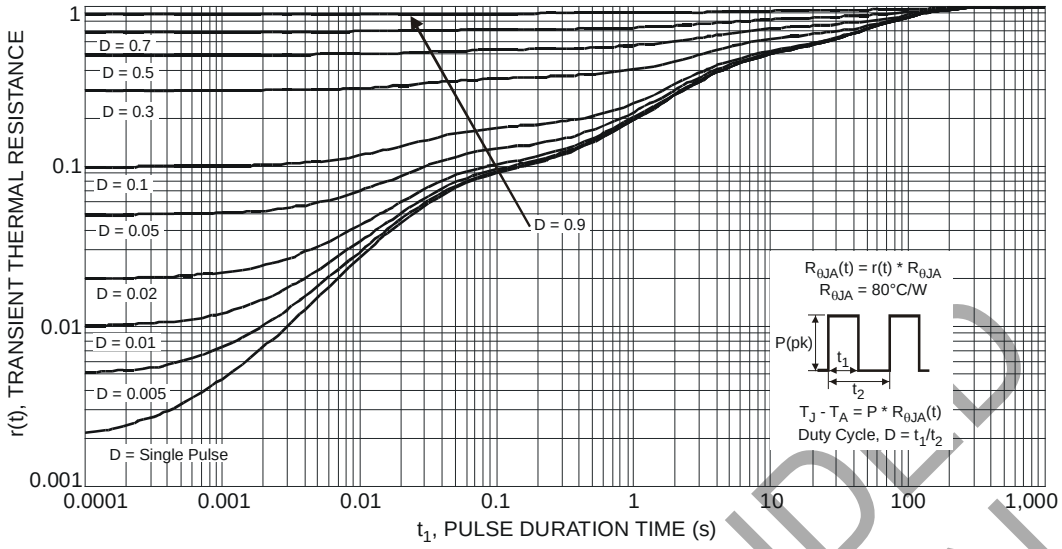
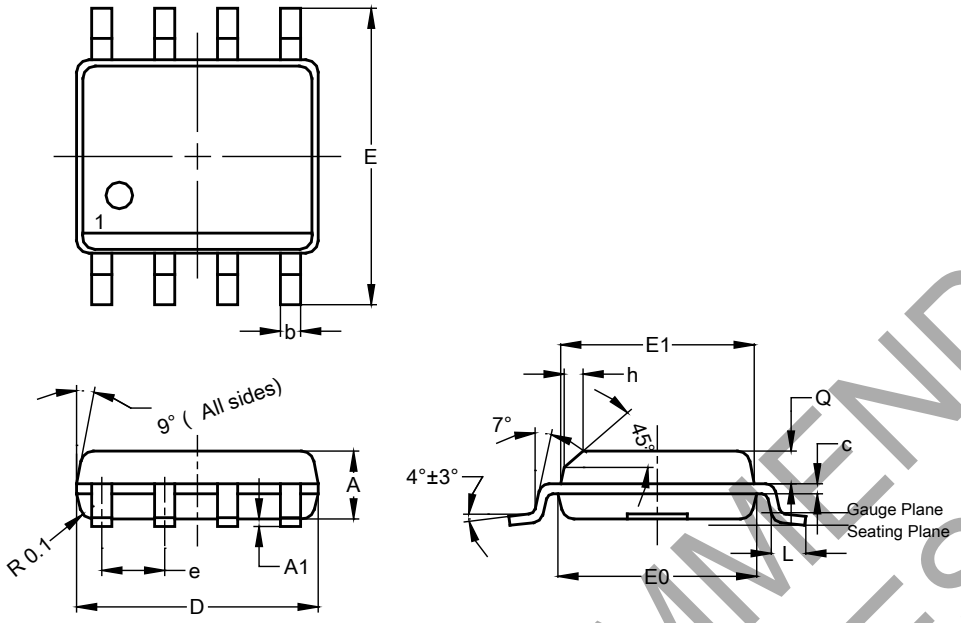


Fig. 12 Transient Thermal Response

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version

SO-8

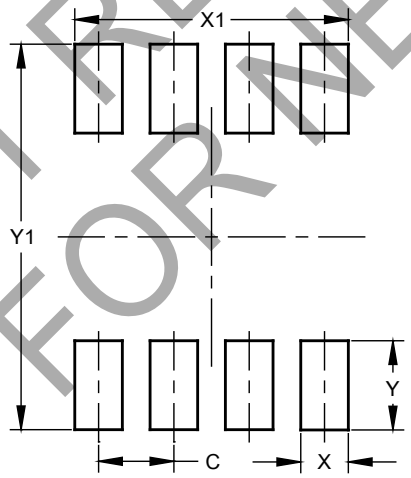


SO-8			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	—	—	1.27
h	—	—	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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